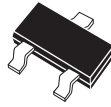


CMPT7410

**SURFACE MOUNT  
PNP SILICON  
LOW  $V_{CE(SAT)}$  TRANSISTOR**



**SOT-23 CASE**

**Central<sup>TM</sup>**  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPT7410 type is a PNP Low  $V_{CE(SAT)}$  silicon transistor manufactured by the epitaxial planar process and epoxy molded in an SOT-23 surface mount package. This device is designed for battery driven, handheld devices requiring high current and Low  $V_{CE(SAT)}$  voltages.

**MARKING CODE: C741**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	1.0	A
Collector Current (Peak)	$I_{CM}$	1.5	A
Power Dissipation	$P_D$	350	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	357	$^\circ\text{C/W}$

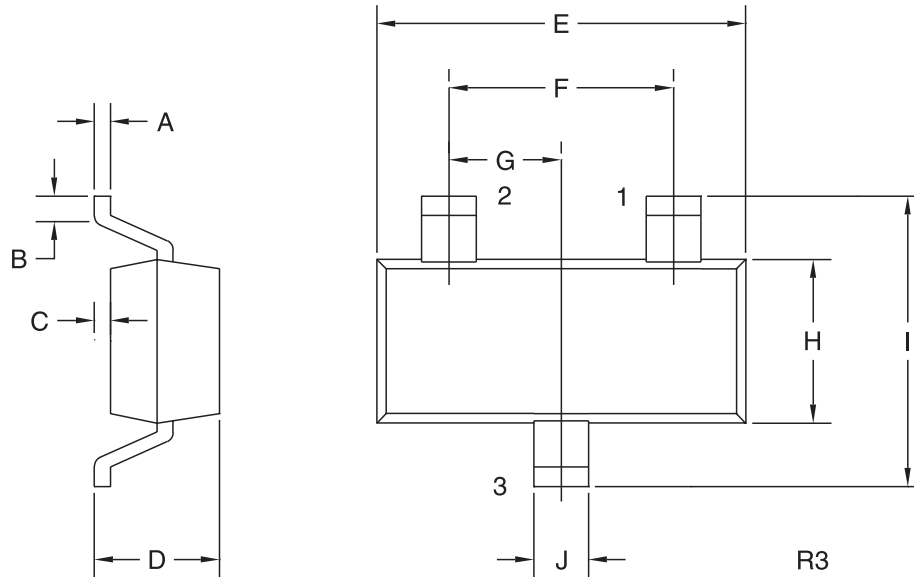
**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{CBO}$	$V_{CB}=40\text{V}$			100	nA
$I_{EBO}$	$V_{EB}=6.0\text{V}$			100	nA
$BV_{CBO}$	$I_C=100\mu\text{A}$	40			V
$BV_{CEO}$	$I_C=10\text{mA}$	25			V
$BV_{EBO}$	$I_E=100\mu\text{A}$	6.0			V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		25	50	mV
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		40	75	mV
$V_{CE(SAT)}$	$I_C=200\text{mA}, I_B=20\text{mA}$		80	150	mV
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		150	250	mV
$V_{CE(SAT)}$	$I_C=800\text{mA}, I_B=80\text{mA}$		220	400	mV
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		275	450	mV
$V_{BE(SAT)}$	$I_C=800\text{mA}, I_B=80\text{mA}$			1.1	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$			0.9	V
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100			
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	100		300	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	100			
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=1.0\text{A}$	50			
$f_T$	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	100			MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$			15	pF

R0 (12-November 2004)

**SURFACE MOUNT  
PNP SILICON  
LOW  $V_{CE}$  (SAT) TRANSISTOR**

**SOT-23 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

**MARKING CODE: C741**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)